

Form PTO-1449

Docket Number (Specimen)

Application Number

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

TSMC-03-065

10/688,045

Applicant

Huan-Just Lin et al.

Filing Date

10/17/03

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	AGING DATE IF APPROPRIATE
	6258675	7/10/01	Gardner et al.	438	287	12/18/97
	6306715	10/23/01	Chan et al.	438	301	1/8/01
	6492242	12/10/02	See et al.	438	393	7/3/00
	6479403	11/12/02	Tsei et al.	438	778	2/28/02
	6451647	9/17/02	Yang et al.	438	240	3/18/02
	6436838	8/20/02	Ying et al.	438	710	4/21/00

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

	TSMC-01-1248, Ser. No. 10/653,852, Filed 09/03/03, assigned to a common assignee, "Method of Multi-element Compound Deposition by Atomic Layer Deposition for IC Barrier Layer Applications".

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

(Use several sheets if necessary)

ALLEGEDLY

10/688,045

Significant

Huan-Just Lin et al.

Filing Date

10/17/03

Group Art Unit

EXAMINER
INITIAL

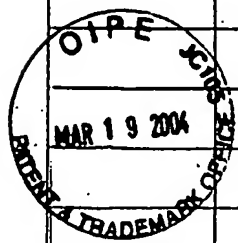
DATE _____

1044

class

SUBCLUE

PLUNO DATE
F APPROPRIATE



DOCUMENT NUMBER

DATE:

COUNTRY

CLASS

SUBCLASS

Translation

YES

NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion(s) Page(s), Etc.)

Co-pending U.S. Patent App. TSMC-02-405,
Serial No. 10/766,596, filed 01/27/04, assigned
to the same assignee, "Zirconium Oxide and
Hafnium Oxide Etching Using Halogen Containing
Chemicals."

ΔΙΛΥΝΕΙΤ

DATE COMPLETED

11/21/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.